EAST Search Hist ry

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	"6133137".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/09 10:13
L2	2	"6613834".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/09 10:13
L3	2	"6958525".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON ,	2006/08/09 10:21
L4	5	123	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/09 10:21
L5	3	4 and (ladder laddershap\$3 siloxane hydride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/09 11:40
L6	4	4 and (ladder laddershap\$3 siloxane hydride hydrogen)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/09 11:43
L7	144591	(si silison gaas) with (carrier substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/09 10:36
L8 -	0	6 and 7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/09 10:35

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L9	208806	(si silison gaas) with (carrier substrate layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/09 10:38
L10	0	6 and 9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/09 10:38
L11	238674	(si silison gaas) with (carrier film substrate layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/09 10:38
L12	1	6 and 11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	^h ON	2006/08/09 10:38
L13	823992	(si silison gaas semiconductor) with (carrier substrate layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON ,	2006/08/09 11:41
L14	2	13 and 6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/09 11:11
L15	2	13 and 6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT;	OR	ON	2006/08/09 11:11
L16	85802	13 and (ladder laddershap\$3 siloxane hydride hydrogen)	IBM_TDB US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/09 11:41

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L17	2527	16 and ladder	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON ,	2006/08/09 11:41
L18	1027736	(si silicon gaas semiconductor) with (carrier substrate layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/09 11:41
L19	122129	18 and (ladder laddershap\$3 siloxane hydride hydrogen)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/09 11:42
L20	3507	ladder and 19	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/09 11:42
L21	280	20 and siloxane and (hydride hydrogen)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/09 11:43
L22	185	oxygen and silicon and 21	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/09 11:45
L23	69	22 and (dielectric with constant)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR ,	*ON	2006/08/09 11:45